

SCOTTSDALE DIVISION

USB50803C thru USB50824C, e3

Bidirectional Low Capacitance TVSarray ™

DESCRIPTION

This Transient Voltage Suppressor (TVS) array is packaged in an SO-8 configuration giving protection to 2 Bidirectional data or interface lines. It is designed for use in applications where very low capacitance protection is required at the board level from voltage transients caused by electrostatic discharge (ESD) as defined in IEC 61000-4-2, electrical fast transients (EFT) per IEC 61000-4-4 and effects of secondary lightning. It is also available with either Tin-Lead plated terminations or as RoHS Compliant with annealed matte-Tin finish by adding an "e3" suffix to the part number*.

Using the schematic on the second page, pins 1 & 2 are tied together for the first protected line, and pins 7 & 8 are tied together to the ground. The same would then occur for a second protected line where pins 3 & 4 are tied together and pins 5 & 6 are tied together to the ground. These may also be switched in polarity connections since the electrical features are the same in each antiparallel (opposite facing) leg when the pins are tied together in this manner for bidirectional protection.

These TVS arrays have a peak power rating of 500 watts for an 8/20 usec pulse. This array is suitable for protection of sensitive circuitry consisting of TTL, CMOS DRAM's, SRAM's, HCMOS, HSIC microprocessors, UNIVERSAL SERIAL BUS (USB) and I/O transceivers. The USB508XXC product provides board level protection from static electricity and other induced voltage surges that can damage or upset sensitive circuitry.

APPEARANCE



SO-8

IMPORTANT: For the most current data, consult MICROSEMI's website: http://www.microsemi.com

FEATURES

- Protects up to 2 bidirectional lines
- Surge protection per IEC 61000-4-2, IEC 61000-4-4
- Provides electrically isolated protection
- UL 94V-0 Flamability Classification
- RoHS Compliant devices available by adding "e3" suffix
- ULTRA LOW CAPACITANCE 3 pF per line pair
- **ULTRA LOW LEAKAGE**

APPLICATIONS / BENEFITS

- EIA-RS485 data rates:
 - 5 Mbs
- 10 Base T Ethernet
- USB date rate: 900 Mbs
- Tape & Reel per EIA Standard 481
- 13 inch reel; 2,500 pieces (OPTIONAL)
- Carrier tubes; 95 pcs (STANDARD)

MAXIMUM RATINGS

- Operating Temperature: -55°C to +150°C
- Storage Temperature: -55°C to +150°C
- Peak Pulse Power: 500 watts (8/20 µs, Figure 1)
- Pulse Repetition Rate: < .01%

15C

24C

Solder Temperatures: 260°C for 10 s (maximum)

15.0

16 7

ELECTRICAL CHARACTERISTICS

MECHANICAL AND PACKAGING

- Molded SO-8 Surface Mount
- Weight 0.066 grams (approximate)
- Marking: Logo, device marking code*, date code
- Pin #1 defined by dot on top of package

1

3

BREAKDOWN CLAMPING CLAMPING CAPACITANCE TEMPERATURE STANDRY STANDOFF VOLTAGE VOLTAGE CURRENT (f=1 MHz) VOLTAGE COEFFICIENT VOLTAGE OF V_{BR} V_C @ 1 Amp DEVICE VRD V_c @ 5 Amp I_D @ V_{WM} PART @1 mA @0V α_{VBR} MARKING' NUMBER (Figure 2) (Figure 2) **VOLTS VOLTS VÖLTS VÖLTS** uА pΕ mV//°C MAX MIN MAX MAX MAX MAX MAX USB50803C 3С 3.3 4 8 200 11 3 40 USB50805C 5C 6.0 13 5.0 10.8 3 1 3 USB50812C 12C 1 12.0 13.3 19 26 8

32

24

USB50815C

USB50824C

11

⁴³ Device marking has an e3 suffix added for the RoHS Compliant option, e.g. 3Ce3, 5Ce3, 12Ce3, 15Ce3, and 24Ce3.



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SYMBOLS & DEFINITIONS						
Symbol	Definition					
V _{WM}	Standoff Voltage: Maximum dc voltage that can be applied over the operating temperature range.					
	V _{WM} must be selected to be equal or be greater than the operating voltage of the line to be protected.					
V_{BR}	Minimum Breakdown Voltage: The minimum voltage the device will exhibit at a specified current					
V _C	Clamping Voltage: Maximum clamping voltage across the TVS device when subjected to a given current at a					
	pulse time of 20 µs.					
I_{D}	Standby Current: Leakage current at V _{WM.}					
С	Capacitance: Capacitance of the TVS as defined @ 0 volts at a frequency of 1 MHz and stated in picofarads.					

GRAPHS

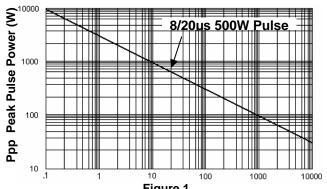


Figure 1
Peak Pulse Power Vs Pulse Time t = µsec

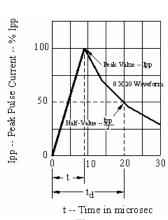
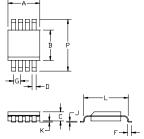


Figure 2
Pulse Wave Form

OUTLINE AND SCHEMATIC



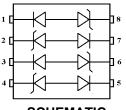
DIM	INCHES		MILLIMETERS	
DIIVI	MIN	MAX	MIN	MAX
Α	0.188	0.197	4.77	5.00
В	0.150	0.158	3.81	4.01
С	0.053	0.069	1.35	1.75
D	0.011	0.021	0.28	0.53
F	0.0160	0.050	0.41	1.27
G	0.050 BSC		1.27 BSC	
J	0.006	0.010	0.15	0.25
K	0.004	0.008	0.10	0.20
Ĺ	0.189	0.206	4.80	5.23
Р	0.228	0.244	5.79	6.19

0.045" +/- .005"

0.245"

0.160" +/- .005"

PAD LAYOUT



SCHEMATIC

OUTLINE